

Title (en)  
Integrated device including a metal- insulator-metal capacitor

Title (de)  
Integriertes Bauelement mit Metall-Isolator-Metall-Kondensator

Title (fr)  
Dispositif intégré comportant un condensateur métal-isolation-métal

Publication  
**EP 1130654 A1 20010905 (DE)**

Application  
**EP 00104264 A 20000301**

Priority  
EP 00104264 A 20000301

Abstract (en)  
In order to produce an integrated component comprising an integrated metal-insulator-metal capacitor (7), a dielectric intermediate layer (11) and an upper electrode (12) are firstly deposited on a copper lower electrode (6) in such a manner that they cover the entire surface. The metal-insulator-metal capacitor (7) is subsequently structured with etch stop in the dielectric intermediate layer (11). The results in preventing short circuits between the upper electrode (12) and the lower electrode (6).

Abstract (de)  
Zur Herstellung eines integrierten Bauelements mit integrierten Metall-Isolator-Metall-Kondensators (7) wird zunächst auf eine untere Elektrode (6) aus Kupfer eine dielektrische Zwischenschicht (11) und eine obere Elektrode (12) ganzflächig abgeschieden. Anschließend erfolgt die Strukturierung des Metall-Isolator-Metall-Kondensators (7) mit Ätzstop in der dielektrischen Zwischenschicht (11). Dadurch werden Kurzschlüsse zwischen der oberen Elektrode (12) und der unteren Elektrode (6) vermieden. <IMAGE>

IPC 1-7  
**H01L 29/92**; **H01L 21/02**

IPC 8 full level  
**H01L 21/768** (2006.01); **H01L 21/02** (2006.01); **H01L 21/3205** (2006.01); **H01L 21/822** (2006.01); **H01L 23/52** (2006.01); **H01L 27/04** (2006.01); **H01L 29/92** (2006.01)

CPC (source: EP KR US)  
**H01L 23/5223** (2013.01 - EP US); **H01L 28/60** (2013.01 - EP US); **H10B 12/00** (2023.02 - KR); **H01L 21/76838** (2013.01 - EP US); **H01L 2924/0002** (2013.01 - EP US)

C-Set (source: EP US)  
**H01L 2924/0002** + **H01L 2924/00**

Citation (search report)

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**EP 00104264 A 20000301**; CN 01805980 A 20010219; EP 0101853 W 20010219; EP 01919307 A 20010219; JP 2001564400 A 20010219; KR 20027011177 A 20020826; TW 90106055 A 20010315; US 23723002 A 20020903